

grooves 165 formed in the first conductive layer 110 can be seen engaging a plurality of [tongues170] tongues 170 formed in the conductive layer 120. A plurality of tongues 180 is also formed in the first conductive layer 110, which overlap the tongues 170 of the second conductive layer 120, and engage the grooves 155. However, in this case, while the shape of the grooves 165 complements the shape of the tongues 170, and the shape of the grooves 155 complements the shape of the tongues 180, the shapes of the interstices 150, 160 are non-complementary, and different than any other heretofore discussed. Here some of the interstices are formed into U shapes (interstices 160), and some of the interstices are formed into box or square shapes (interstices 150). Thus, instead of characterizing the shape of the interstices 150, 160 with any particular dimensions, or ratios of dimensions (e.g., the depth D1 is twice as deep as the width H1, or the tongue thickness T1 is one-third of the width H1), it may also be useful to characterize the shape of individual interstices as that of commonly known geometric shapes or alphabetic characters, such as U shaped, triangular shaped, square shaped, elliptically or oval shaped, etc.

**The paragraph beginning on page 25, line 17 is amended as follows:**

After the first set of interstices or grooves are formed in block 430, the second interstice, or second plurality of interstices can be formed (and if desired at this time, engaged with the first interstice, or first plurality of interstices), according to block 440. If the tongue and groove approach is taken, then one or more tongues can now be formed in the second conductive layer, so as to engage the corresponding grooves in the first conductive layer. In either case, the second set of interstices or tongues will be formed according to the shapes chosen in block 400, and whether complementary shapes [where] were chosen (block 410) or non-complementary shapes were chosen (block 420). The size of the second set of interstices, or the tongues formed in the second conductive layer will usually be determined by the size of the first set of interstices, or grooves, formed in the first conductive layer in accordance with block 430, along with the materials selected for the first and second conductive layers, and the dielectric layer (see blocks 470 and 480).

**PRELIMINARY AMENDMENT**

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Page 3

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The Examiner is invited to contact the below-signed attorney with any questions regarding the present application.

Respectfully submitted,

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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner of Patents, Washington, D.C. 20231, on this 30 day of November, 2001.

Name

Tina Pugh

Signature

